

AMENDMENTS TO THE CLAIMS

Claim 1 (Cancelled)

2. (Previously Presented) The electrostatic chucking system according to claim 6, further comprising a temperature sensor for detecting the temperature of the semiconductor substrate held by said electrostatic chuck, wherein a signal output from said temperature sensor is input to said voltage control section to thereby control the applied voltage.

Claims 3-4 (Cancelled)

5. (Previously Presented) The electrostatic chucking system according to claim 6, wherein the control of variation in the applied voltage involves either increase or decrease in voltage.

6. (Previously Presented) An electrostatic chucking system comprising:
an electrostatic chuck having an electrode for chucking a semiconductor substrate;
a power supply section for applying a voltage to said electrode; and
a voltage control section for controlling the applied voltage, wherein
said voltage control section varies and controls the applied voltage stepwise, and wherein
the applied voltage is controlled such that a rate at which the temperature change of the semiconductor substrate falls with a range of 10°C/sec. to 150°C/sec.

7. (Previously Presented) A method of manufacturing a semiconductor device comprising a step of treating a semiconductor wafer through use of the electrostatic system according to claim 6.

8. (Previously Presented) An apparatus for manufacturing a semiconductor device, said apparatus comprising the electrostatic system according to claim 6.